

Supporting Information

Thermoelectric properties of *n*-type Cu₄Sn₇S₁₆-based compounds

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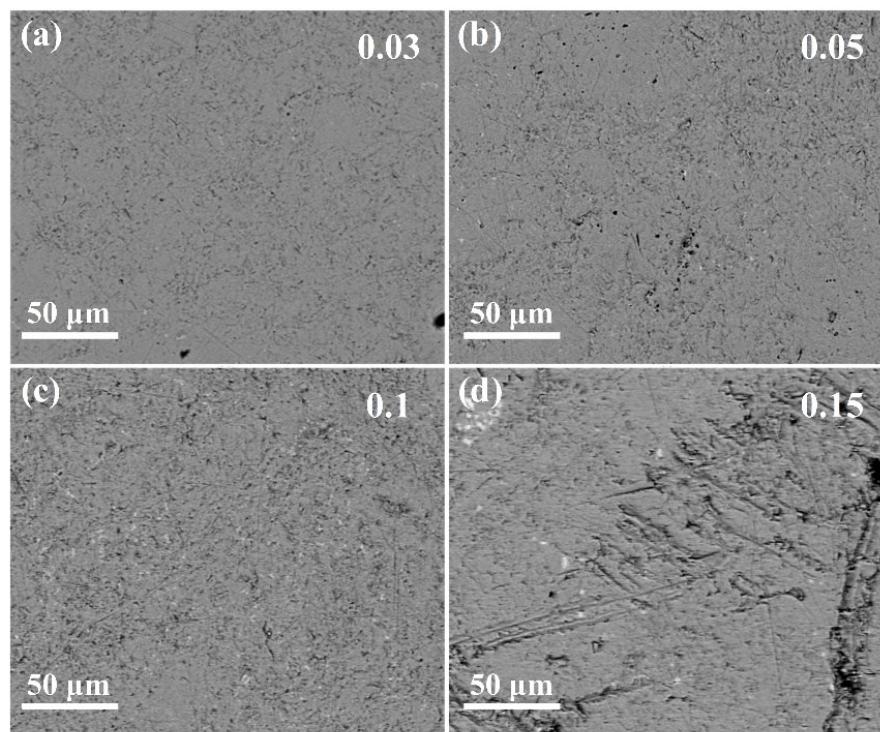


Fig. S1 Backscattered electron (BSE) patterns of Cu_{4-x}Ag_xSn₇S₁₆ ($x = 0.03, 0.05, 0.1, 0.15$). Impurity phases (white particles) emerge when x reaches 0.05.

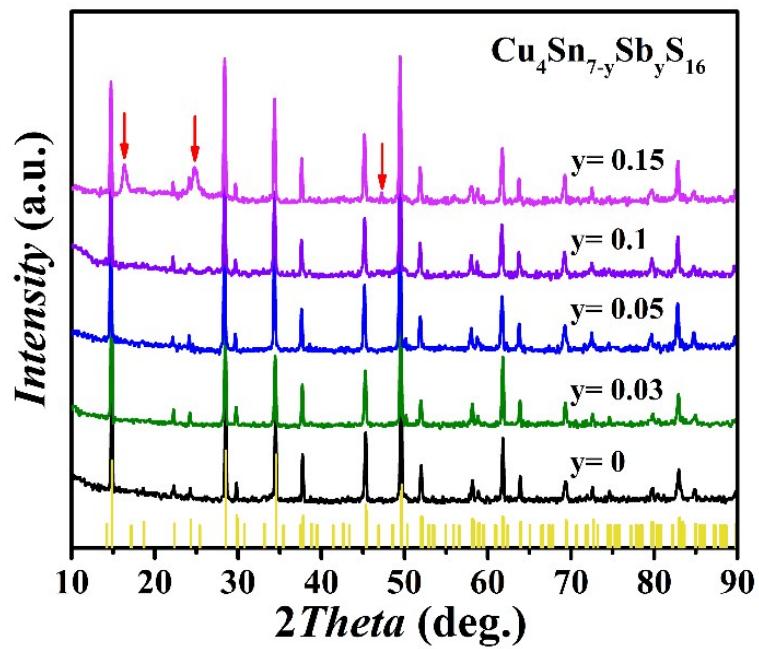


Fig. S2 XRD patterns of $\text{Cu}_4\text{Sn}_{7-y}\text{Sb}_y\text{S}_{16}$ ($y = 0, 0.03, 0.05, 0.1, 0.15$) bulks after SPS.

Impurity phases emerge when y reaches 0.15.

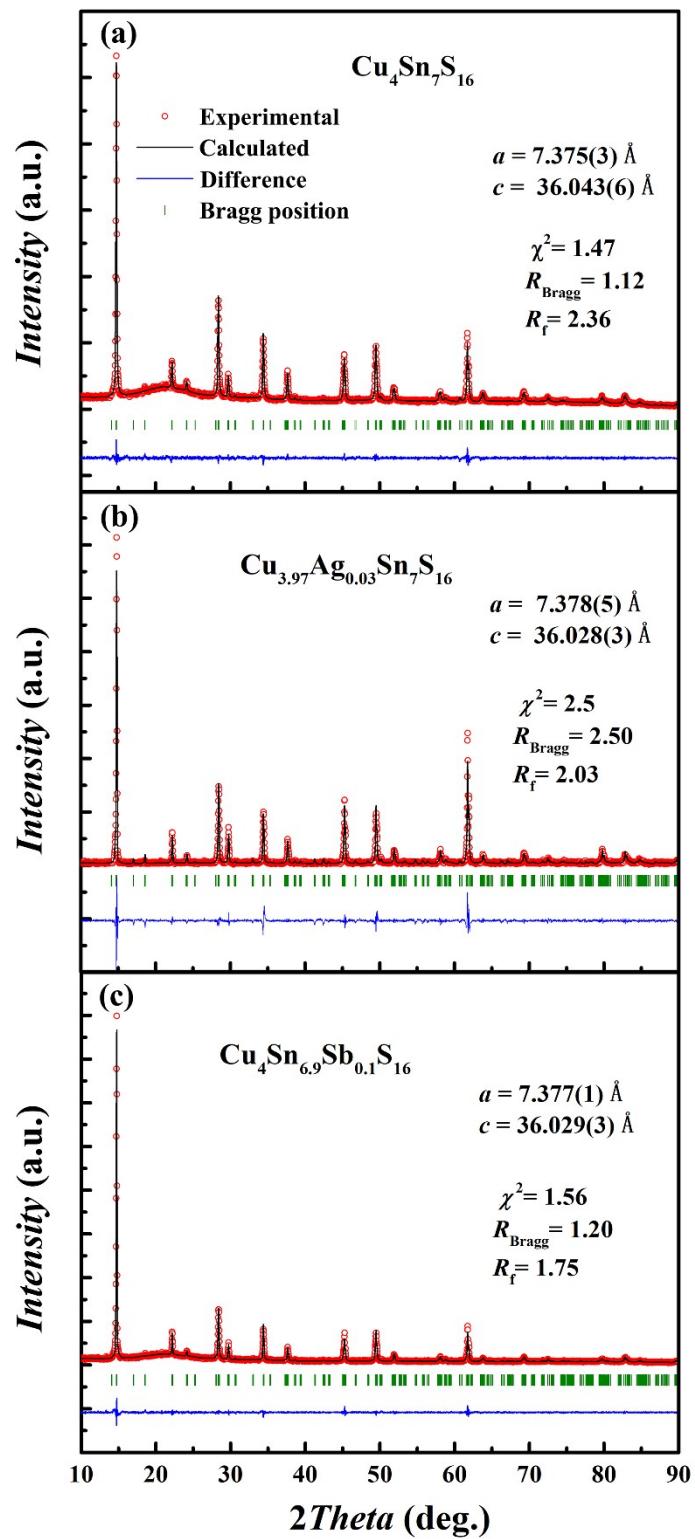


Fig. S3 Rietveld refinements for (a) $\text{Cu}_4\text{Sn}_7\text{S}_{16}$; (b) $\text{Cu}_{3.97}\text{Ag}_{0.03}\text{Sn}_7\text{S}_{16}$; (c) $\text{Cu}_4\text{Sn}_{6.9}\text{Sb}_{0.1}\text{S}_{16}$

Table S1 Refined lattice parameters for Cu₄Sn₇S₁₆, Cu_{3.97}Ag_{0.03}Sn₇S₁₆ and Cu₄Sn_{6.9}Sb_{0.1}S₁₆

	Cu ₄ Sn _{6.9} Sb _{0.1} S ₁₆		
	Cu ₄ Sn ₇ S ₁₆	Cu _{3.97} Ag _{0.03} Sn ₇ S ₁₆	Cu ₄ Sn _{6.9} Sb _{0.1} S ₁₆
<i>a</i> (Å)	7.375	7.379	7.378
<i>c</i> (Å)	36.04	36.03	36.03
<i>V</i> _{cell} (Å ³)	1697.94	1698.69	1698.12